

NO.1188D

LB1231 Series

High-Voltage, Large Current Darlington Transistor Array

The circuit configuration of this IC is of 7-channel Darlington transistor array consisting of NPN transistors. It is especially suited for use in hammer drivers and lamp, relay drivers. It contains spark killer diodes against L load.

Features High-voltage (VCEO≥50V),large-current (ICmax=500mA) drive

LB1231 . Drivable by TTL, MOS output

LB1232 . Contains base current limiting resistors, Zener diodes for level shift.

. Direct drivable by 24V P MOS.

LB1233 . Contains base current limiting resistors.

. Direct drivable by TTL, C MOS output.

LB1234 . Contains base current limiting resistors.

. Direct drivable by C MOS, P MOS output.

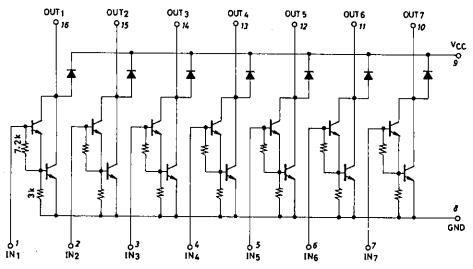
°C			unit
$v_{ ext{OUT}}$		50	V
	Per unit	500	mΑ
V _{IN}	LB1232/33/34	30	V
IIN	LB1231 only	25	mA
IGND	7ch simultaneously	on, 2.8	A
;	f=10Hz,duty,=23%		
$P_{\mathbf{d}}$ max	• •	1.5	W
Topr		-20 to +75	°C
$^{\mathrm{T}}$ stg		-40 to +150	°C
Ta=25°C			unit
		50	v
LB1232	$I_{OUT}=350mA$	11 to 30	V
LB1233	IOUT=350mA	3 to 30	V
LB1234	IOUT=350mA	5 to 30	v
LB1231/3	,	-0.3 to $+0.3$	V
LB1232	IOUT≦100μA	-0.3 to $+6.0$	V
LB1234	IOUT≦100µA	-0.3 to $+0.7$	v
	VIN IIN IGND Pdmax Topr Tstg Ta=25°C LB1232 LB1233 LB1234 LB1231/3 LB1232	VOUT IOUT Per unit VIN LB1232/33/34 IIN LB1231 only IGND 7ch simultaneously f=10Hz,duty,=23% Pdmax Topr Tstg Ta=25°C LB1232 IOUT=350mA LB1233 IOUT=350mA LB1234 IOUT=350mA LB1234 IOUT=350mA LB1231/33 IOUT≤100µA LB1232 IOUT≤100µA	Vout Fer unit 500 Iout Per unit 500 Vin LB1232/33/34 30 Iin LB1231 only 25 IGND 7ch simultaneously on, 2.8 f=10Hz,duty,=23% Pdmax 1.5 Topr -20 to +75 Tstg -20 to +75 Tstg -40 to +150 LB1232 Iout=350mA 11 to 30 LB1234 Iout=350mA 3 to 30 LB1234 Iout=350mA 5 to 30 LB1231/33 Iout≤100μA -0.3 to +0.3 LB1232 Iout≤100μA -0.3 to +6.0

Package Dimensions 3064-D16TR (unit: mm)

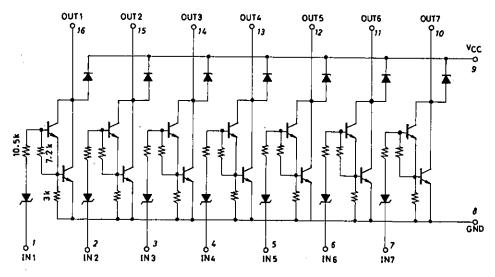
Electrical Characteristics	at Ta=25	°C	min	typ	max	unit
Output Leak Current	IOFF	V _{OUT} =50V		-21	100	ت عدد Au
Output Voltage	v_{OH1}	$I_{IN}=0.25$ mA, $I_{OUT}=100$ mA		0.9	1.1	v
	v_{OH2}	$I_{IN}=0.35$ mA, $I_{OUT}=200$ mA		1.1	1.3	V
	v_{OH3}	I _{IN} =0.5mA, I _{OUT} =350mA		1.3	1.6	V
•	V _{OH4}	IIN=lmA,I _{OUT} =400mA			2.4	V
Input Voltage	$v_{\mathtt{IN}}$	LB1231 IIN=1mA	,	1.35	1.7	v
Input Current	v_{IN}	LB1232 V _{IN} =17V	(2.82	1.25	mA
		LB1233 V _{IN} =3.85V	(0.93	1.35	mA
		LB1234 V _{IN} =5V	4	0.35	0.5	mΑ
		LB1234 VIN=12V		1.00	1.45	mΑ
Spark Killer Diode Leak Currnet	IR(S)	$V_{R(S)}=50V$			100	Aυζ
Spark Killer Diode 🗀 🤫	V _F (S)1	$I_{F(S)} = 350 \text{mA}$			2.0	V
Forward Voltage	VF(S)2	$I_F(s) = 400 \text{mA}$			2.4	v

Equivalent Circuits LB1231

Unit (resistance: Ω)



LB1232

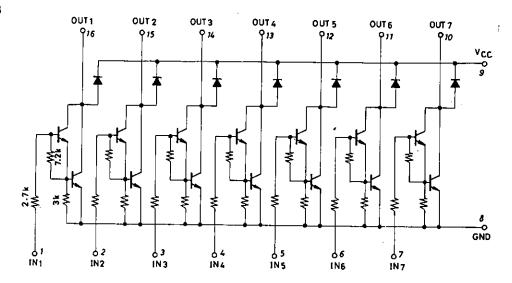


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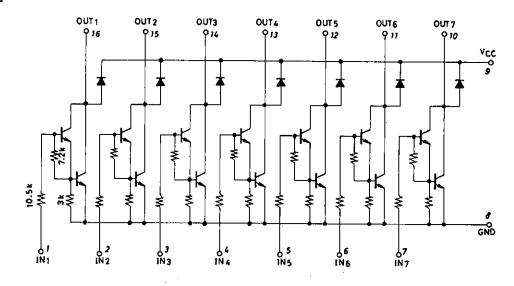
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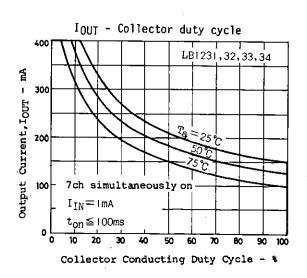
Unit (resistance: Ω)

LB1233



LB1234





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